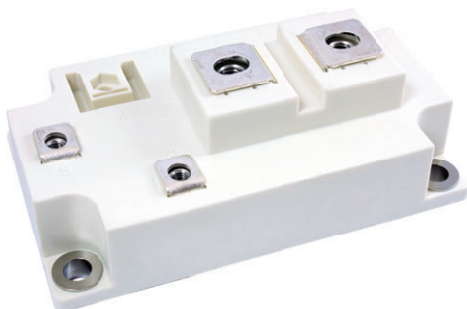


Molding Type Module IGBT, 1-in-1 Package, 1200 V and 600 A



Dual INT-A-PAK

FEATURES

- High short circuit capability, self limiting to $6 \times I_C$
- 10 μ s short circuit capability
- $V_{CE(on)}$ with positive temperature coefficient
- Low inductance case
- Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TYPICAL APPLICATIONS

- AC inverter drives
- Switching mode power supplies
- Electronic welder at f_{sw} up to 20 kHz

DESCRIPTION

Vishay's IGBT power module provides ultralow conduction loss as well as short circuit ruggedness. It is designed for applications such as inverters and UPS.

PRIMARY CHARACTERISTICS	
V_{CES}	1200 V
I_C at $T_C = 80^\circ\text{C}$	600 A
$V_{CE(on)}$ (typical) at $I_C = 600\text{ A}$, 25°C	1.9 V
Speed	8 kHz to 30 kHz
Package	Dual INT-A-PAK
Circuit configuration	Single switch with AP diode

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Gate to emitter voltage	V_{GES}		± 20	
Collector current at $T_J = 150^\circ\text{C}$	I_C	$T_C = 25^\circ\text{C}$	910	A
		$T_C = 80^\circ\text{C}$	600	
Pulsed collector current	$I_{CM}^{(1)}$	$T_C = 80^\circ\text{C}$	1200	
Diode continuous forward current	I_F		600	
Diode maximum forward current	I_{FM}		1200	
Maximum power dissipation	P_D	$T_J = 150^\circ\text{C}$	3125	W
Short circuit withstand time	t_{SC}	$T_J = 125^\circ\text{C}$	10	μ s
RMS isolation voltage	V_{ISOL}	$f = 50\text{ Hz}$, $t = 1\text{ min}$	2500	V
I^2t -value, diode	I^2t	$V_R = 0\text{ V}$, $t = 10\text{ ms}$, $T_J = 125^\circ\text{C}$	74 000	A^2s

Note

(1) Repetitive rating; pulse width limited by maximum junction temperature.

IGBT ELECTRICAL SPECIFICATIONS ($T_C = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$T_J = 25^\circ\text{C}$	1200	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 600\text{ A}$, $T_J = 25^\circ\text{C}$	-	1.9	-	
		$V_{GE} = 15\text{ V}$, $I_C = 600\text{ A}$, $T_J = 125^\circ\text{C}$	-	2.1	-	
Gate to emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GES}$, $I_C = 24\text{ mA}$, $T_J = 25^\circ\text{C}$	5.0	6.2	7.0	
Collector cut-off current	I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{ V}$, $T_J = 25^\circ\text{C}$	-	-	5.0	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0\text{ V}$, $T_J = 25^\circ\text{C}$	-	-	400	nA

**SWITCHING CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 600\text{ A}$, $R_g = 3\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$	-	200	-	ns
Rise time	t_r		-	62	-	
Turn-off delay time	$t_{d(off)}$		-	510	-	
Fall time	t_f		-	60	-	
Turn-on switching loss	E_{on}		-	39	-	mJ
Turn-off switching loss	E_{off}		-	48	-	
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 600\text{ A}$, $R_g = 3\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	210	-	ns
Rise time	t_r		-	65	-	
Turn-off delay time	$t_{d(off)}$		-	600	-	
Fall time	t_f		-	75	-	
Turn-on switching loss	E_{on}		-	45	-	mJ
Turn-off switching loss	E_{off}		-	60	-	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$, $V_{CE} = 25\text{ V}$, $f = 1.0\text{ MHz}$	-	41.0	-	nF
Output capacitance	C_{oes}		-	3.1	-	
Reverse transfer capacitance	C_{res}		-	2.0	-	
SC data	I_{SC}	$t_{SC} \leq 10\ \mu\text{s}$, $V_{GE} = 15\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$, $V_{CC} = 900\text{ V}$, $V_{CEM} \leq 1200\text{ V}$	-	2600	-	A
Stray inductance	L_{CE}		-	-	20	nH
Module lead resistance, terminal to chip	$R_{CC'+EE'}$	$T_C = 25\text{ }^\circ\text{C}$	-	0.18	-	m Ω

DIODE ELECTRICAL SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Diode forward voltage	V_F	$I_F = 600\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	- 1.8 1.9	2.4 - -	V
Diode reverse recovery charge	Q_{rr}	$I_F = 600\text{ A}$, $V_R = 600\text{ V}$, $di_F/dt = -6000\text{ A}/\mu\text{s}$, $V_{GE} = -15\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	- 65 100	- - -	μC
Diode peak reverse recovery current	I_{rr}		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	- 450 510	- - -	A
Diode reverse recovery energy	E_{rec}		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	- 35 42	- - -	mJ

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating temperature range	T _J		-40	-	150	°C
Storage temperature range	T _{Stg}		-40	-	125	°C
Junction to case per module	R _{thJC}	IGBT	-	-	0.04	K/W
		Diode	-	-	0.09	
Case to sink	R _{thCS}	Conductive grease applied	-	0.035	-	
Mounting torque		Power terminal screw: M6	2.5 to 5.0			Nm
		Mounting screw: M6	3.0 to 6.0			
Weight			310			g

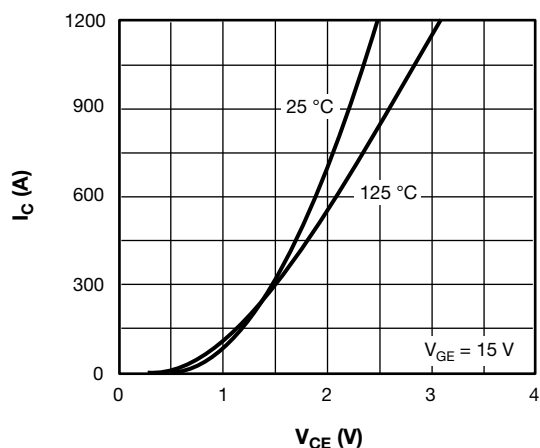


Fig. 1 - Typical Output Characteristics

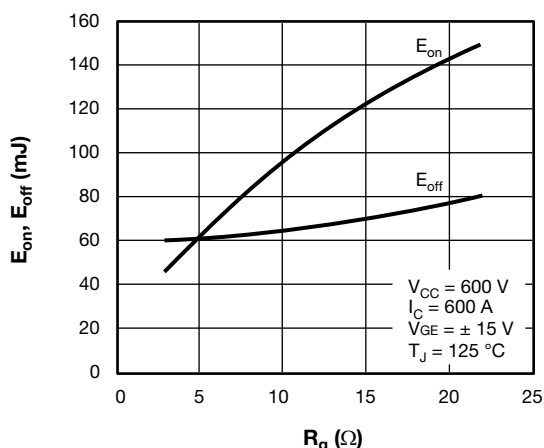


Fig. 4 - Switching Loss vs. Gate Resistor

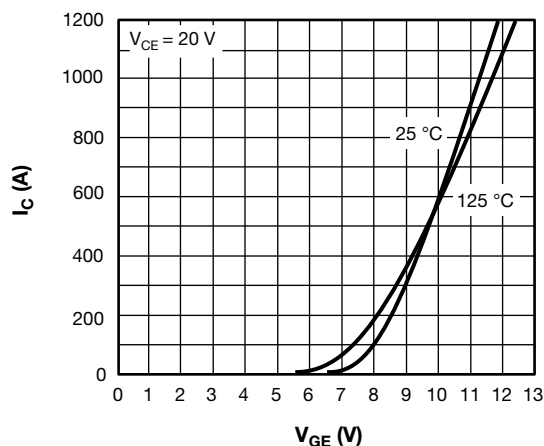


Fig. 2 - Typical Transfer Characteristics

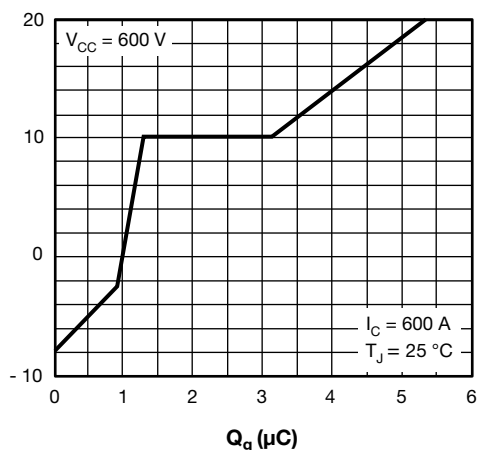


Fig. 5 - Gate Charge Characteristics

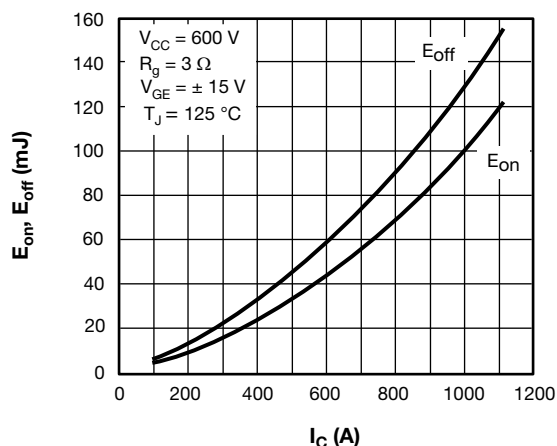


Fig. 3 - Switching Loss vs. Collector Current

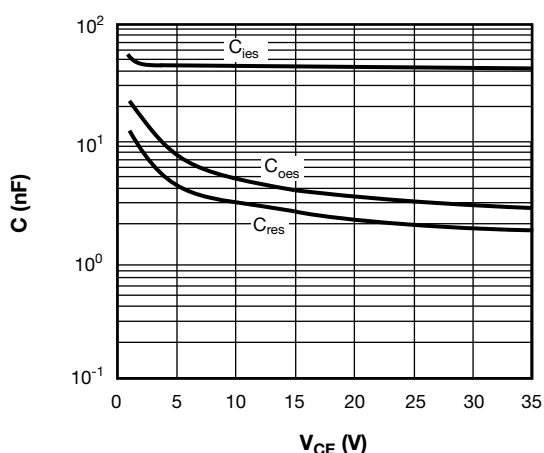


Fig. 6 - Typical Capacitance vs. Collector-Emitter Voltage

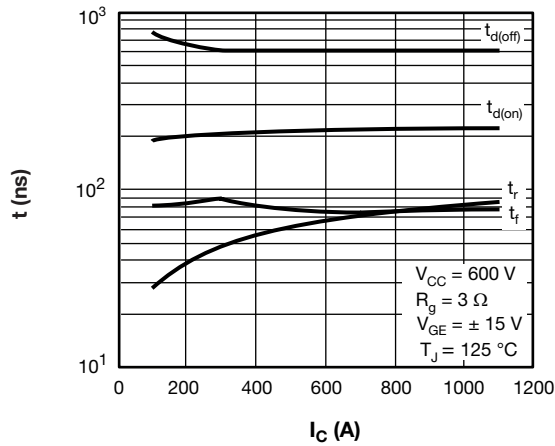


Fig. 7 - Typical Switching Times

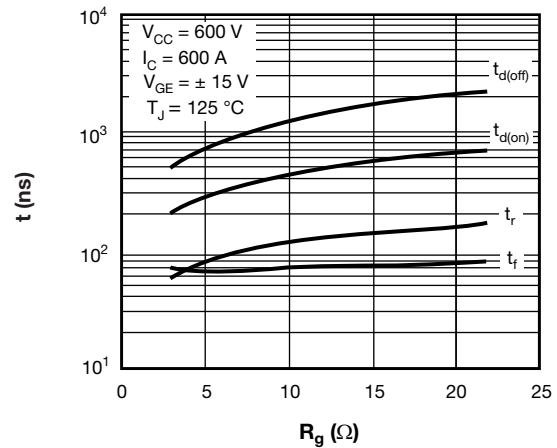
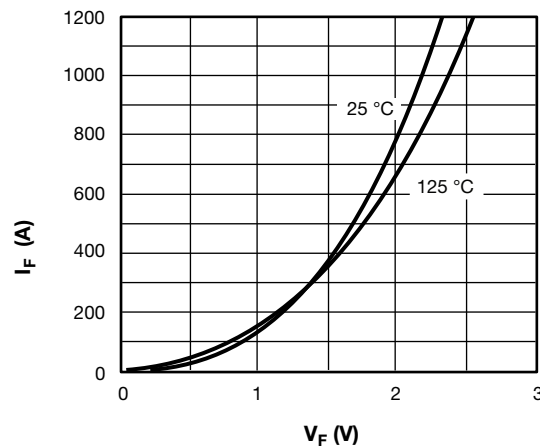

Fig. 8 - Typical Switching Times vs. Gate Resistance R_g


Fig. 9 - Typical forward Characteristics (Diode)

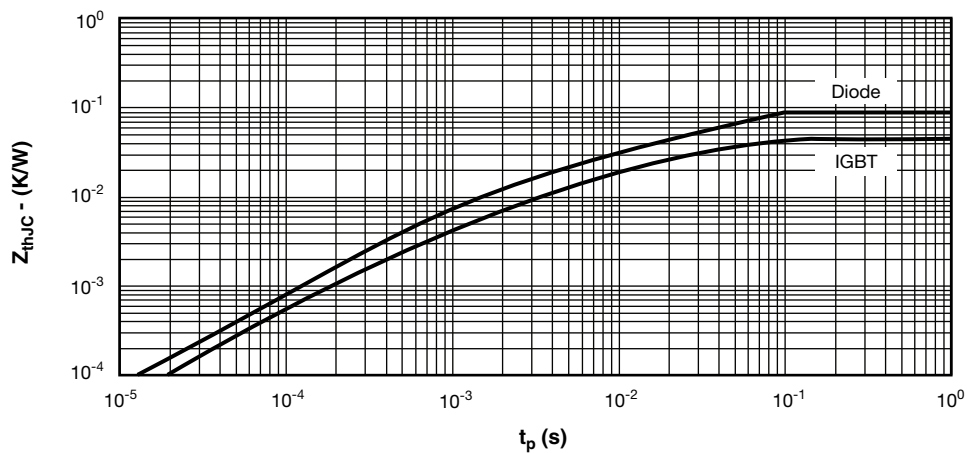
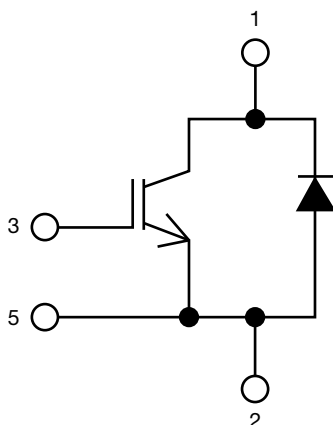


Fig. 10 - Transient Thermal Impedance



CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS

Dimensions		www.vishay.com/doc?95526
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